

Silicon Epitaxial Planar Switching Diode

Features

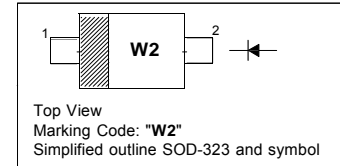
- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications

- Ultra high speed switching

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|-----------------------------------|-------------|---------------|------------------|
| Maximum (Peak) Reverse Voltage | V_{RM} | 85 | V |
| Reverse Voltage | V_R | 80 | V |
| Average Rectified Forward Current | $I_{F(AV)}$ | 100 | mA |
| Maximum (Peak) Forward Current | I_{FM} | 200 | mA |
| Surge Forward Current (10 ms) | I_{FSM} | 1 | A |
| Power Dissipation | P_{tot} | 150 | mW |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Max. | Unit |
|--|----------|------------|---------------|
| Forward Voltage at $I_F = 100\text{ mA}$ | V_F | 1.2 | V |
| Reverse Current at $V_R = 30\text{ V}$ at $V_R = 80\text{ V}$ | I_R | 0.1 0.5 | μA |
| Total Capacitance at $V_R = 0, f = 1\text{ MHz}$ | C_T | 3 | pF |
| Reverse Recovery Time at $I_F = I_R = 10\text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\ \Omega$ | t_{rr} | 4 | ns |

